

# NCE N-Channel Enhancement Mode Power MOSFET

#### Description

The NCE3080KA uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

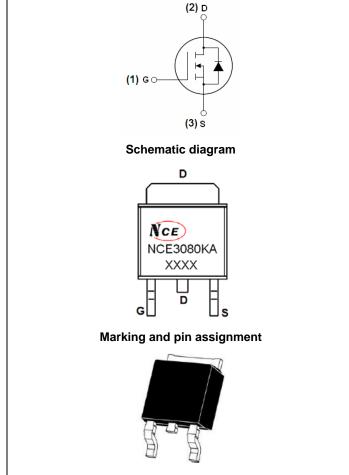
#### **General Features**

- V<sub>DS</sub> =30V,I<sub>D</sub> =80A
  R<sub>DS(ON)</sub> <6.5mΩ @ V<sub>GS</sub>=10V
  R<sub>DS(ON)</sub> < 10mΩ @ V<sub>GS</sub>=5V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E<sub>AS</sub>
- Excellent package for good heat dissipation

### Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

#### 100% UIS TESTED!



TO-252-2L top view

#### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE3080KA	NCE3080KA	TO-252-2L	-	-	-

#### Absolute Maximum Ratings (T<sub>c</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	30	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I <sub>D</sub>	80	А
Drain Current-Continuous(T <sub>C</sub> =100 °C)	l <sub>D</sub> (100℃)	50	A
Pulsed Drain Current	I <sub>DM</sub>	170	A
Maximum Power Dissipation	PD	83	W
Derating factor		0.56	<b>W</b> /℃
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	306	mJ
Operating Junction and Storage Temperature Range	$T_J,T_STG$	-55 To 175	°C



#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{ extsf{ heta}JC}$	1.8	°C/W

#### **Electrical Characteristics (Tc=25**°C unless otherwise noted)

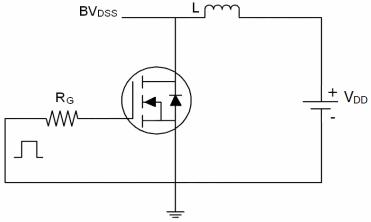
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·		•	•		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	30	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)			•			
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA	0.7	1.1	1.4	V
Drain-Source On-State Resistance	В	V <sub>GS</sub> =10V, I <sub>D</sub> =30A	-	5.5	6.5	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =5V, I <sub>D</sub> =24A	-	7.5	10	
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =5V,I <sub>D</sub> =24A	20	-	-	S
Dynamic Characteristics (Note4)	·		•	•		
Input Capacitance	C <sub>lss</sub>		-	2330	-	PF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =15V,V <sub>GS</sub> =0V, F=1.0MHz	-	460	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	230	-	PF
Switching Characteristics (Note 4)	·					
Turn-on Delay Time	t <sub>d(on)</sub>		-	20	-	nS
Turn-on Rise Time	tr	V <sub>DD</sub> =10V,I <sub>D</sub> =30A	-	15	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10V, $R_{GEN}$ =2.7 $\Omega$	-	60	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	10	-	nS
Total Gate Charge	Qg	<u>)/ −10)/  −204</u>	-	51	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =10V,I <sub>D</sub> =30A, V <sub>GS</sub> =10V	-	14	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	11	-	nC
Drain-Source Diode Characteristics	·					
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =30A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	80	А
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF = 30A	-	32	50	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	-	12	20	nC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD				

#### Notes:

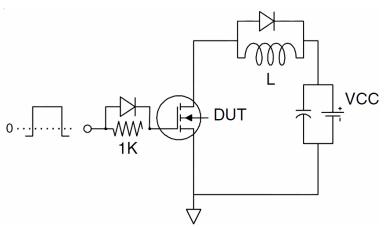
- **1.** Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- **3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition: Tj=25 $^{\circ}$ C,V<sub>DD</sub>=15V,V<sub>G</sub>=10V,L=0.5mH,Rg=25 $\Omega$



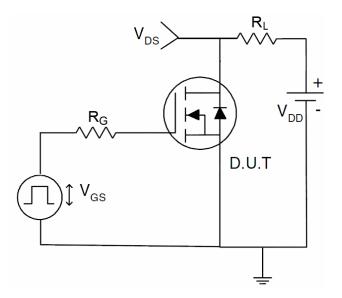
## Test Circuit 1) E<sub>AS</sub> Test Circuits



### 2) Gate Charge Test Circuit:



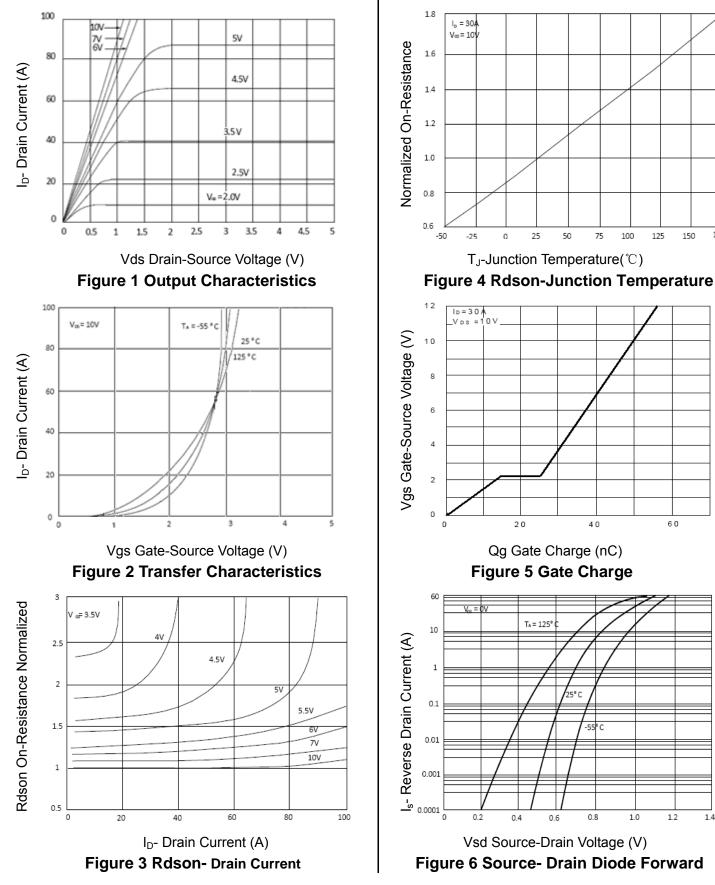
3) Switch Time Test Circuit:





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## **Typical Electrical and Thermal Characteristics (Curves)**

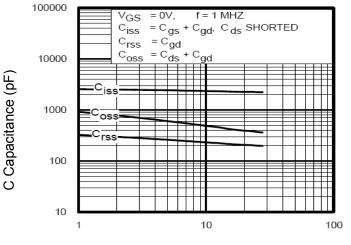


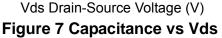
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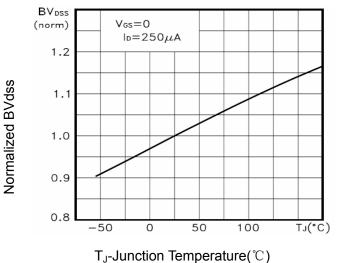
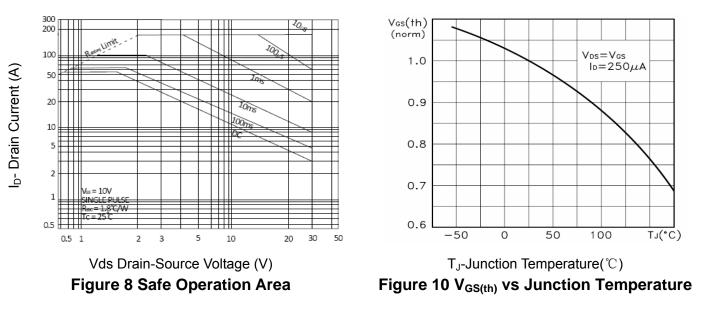
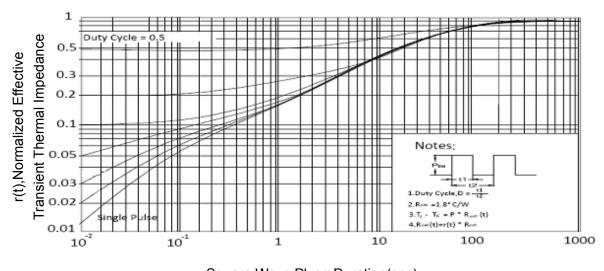


Figure 9 BV<sub>DSS</sub> vs Junction Temperature



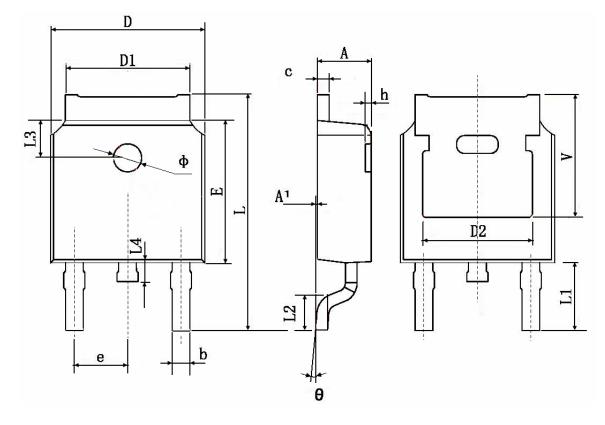


Square Wave Pluse Duration(sec) Figure 11 Normalized Maximum Transient Thermal Impedance



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# **TO-252 Package Information**



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.8	30 TYP.	0.190 TYP.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Φ	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.35	D TYP.	0.211 TYP.		



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